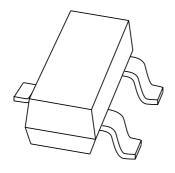
DISCRETE SEMICONDUCTORS

DATA SHEET



BCW61 seriesPNP general purpose transistors

Product data sheet Supersedes data of 1997 May 28 1999 Apr 12



PNP general purpose transistors

BCW61 series

FEATURES

• Low current (max. 100 mA)

• Low voltage (max. 32 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package. NPN complement: BCW60.

MARKING

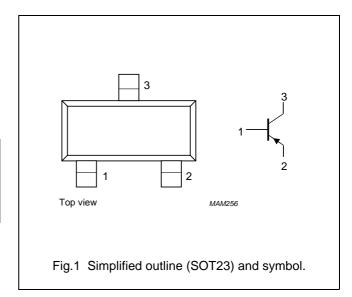
| TYPE NUMBER | MARKING CODE ⁽¹⁾ |
|-------------|-----------------------------|
| BCW61B | BB* |
| BCW61C | BC* |
| BCW61D | BD* |

Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.

PINNING

| PIN | DESCRIPTION | |
|-----|-------------|--|
| 1 | base | |
| 2 | emitter | |
| 3 | collector | |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | _ | -32 | V |
| V _{CEO} | collector-emitter voltage | open base | _ | -32 | V |
| V _{EBO} | emitter-base voltage | open collector | _ | -5 | V |
| I _C | collector current (DC) | | _ | -100 | mA |
| I _{CM} | peak collector current | | _ | -200 | mA |
| I _{BM} | peak base current | | _ | -100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C; note 1 | _ | 250 | mW |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |
| T _{amb} | operating ambient temperature | | -65 | +150 | °C |

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP general purpose transistors

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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT | |
|---------------------|---|------------|-------|------|--|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 500 | K/W | |

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------------|--------------------------------------|---|-------|------|-------|------|
| I _{CBO} | collector cut-off current | $I_E = 0; V_{CB} = -32 \text{ V}$ | _ | _ | -20 | nA |
| | | $I_E = 0$; $V_{CB} = -32 \text{ V}$; $T_{amb} = 150 \text{ °C}$ | _ | _ | -20 | μА |
| I _{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = -4 \text{ V}$ | _ | _ | -20 | nA |
| h _{FE} | DC current gain | $I_C = -10 \mu A; V_{CE} = -5 V$ | | | | |
| | BCW61B | | 30 | _ | _ | |
| | BCW61C | | 40 | _ | _ | |
| | BCW61D | | 100 | _ | _ | |
| | DC current gain | $I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$ | | | | |
| | BCW61B | | 180 | _ | 310 | |
| | BCW61C | | 250 | _ | 460 | |
| | BCW61D | | 380 | _ | 630 | |
| | DC current gain | $I_C = -50 \text{ mA}; V_{CE} = -1 \text{ V}$ | | | | |
| | BCW61B | | 80 | _ | _ | |
| | BCW61C | | 100 | _ | _ | |
| | BCW61D | | 110 | _ | _ | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = -10 \text{ mA}; I_B = -0.25 \text{ mA}$ | -60 | _ | -250 | mV |
| | | $I_C = -50 \text{ mA}; I_B = -1.25 \text{ mA}$ | -120 | _ | -550 | mV |
| V _{BEsat} | base-emitter saturation voltage | $I_C = -10 \text{ mA}; I_B = -0.25 \text{ mA}$ | -600 | _ | -850 | mV |
| | | $I_C = -50 \text{ mA}; I_B = -1.25 \text{ mA}$ | -0.68 | _ | -1.05 | V |
| V_{BE} | base-emitter voltage | $I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$ | -600 | -650 | -750 | mV |
| | | $I_C = -10 \mu A; V_{CE} = -5 V$ | _ | -550 | _ | mV |
| | | $I_C = -50 \text{ mA}; V_{CE} = -1 \text{ V}$ | _ | -720 | _ | mV |
| C _c | collector capacitance | $I_E = i_e = 0; V_{CB} = -10 \text{ V}; f = 1 \text{ MHz}$ | _ | 4.5 | _ | pF |
| C _e | emitter capacitance | $I_C = i_c = 0$; $V_{EB} = -0.5 \text{ V}$; $f = 1 \text{ MHz}$ | _ | 11 | _ | pF |
| f _T | transition frequency | $I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz; note 1 | 100 | _ | _ | MHz |
| F | noise figure | I_C = -200 μA; V_{CE} = -5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz | _ | 2 | 6 | dB |

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

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PNP general purpose transistors

BCW61 series

PACKAGE OUTLINE

UNIT

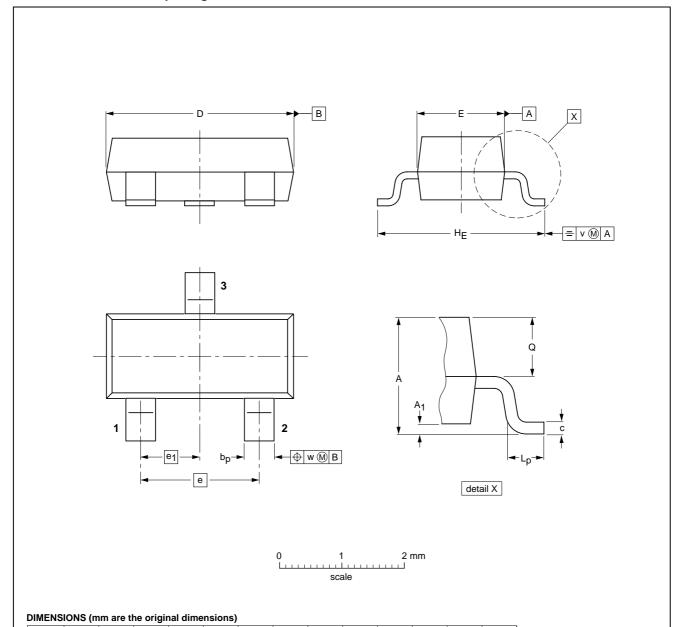
mm

Α

1.1 0.9 max.

Plastic surface mounted package; 3 leads

SOT23



| OUTLINE | | REFER | RENCES | EUROPEAN | ISSUE DATE |
|---------|-----|----------|--------|------------|----------------------|
| VERSION | IEC | JEDEC | EIAJ | PROJECTION | ISSUE DATE |
| SOT23 | | TO-236AB | | | -97-02-28 |

4

Q

0.55 0.45

 L_{p}

0.45 0.15

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С

0.15

0.09

bp

0.48 0.38 D

3.0 2.8 Ε

PNP general purpose transistors

BCW61 series

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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